EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	(low adj4 voltage).with gate with ((read or transfer) near3 transistor$1) with reset$3 with (lower or smaller or higher or larger)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 13:54
L2	31	(potential or voltage) with gate with ((read or transfer) near3 transistor$1) with reset$3 with (lower or smaller or higher or larger)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:40
L3	333	voltage with gate with ((read or transfer) near3 transistor$1) with reset$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:36
L4	956	348/308.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:37
L5	42	3 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:37
L6	290	(potential or voltage) with drain with reset$3 with (lower or smaller or higher or larger)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:44
L7	31	(low near3 (potential or voltage)) with drain with reset$3 with (lower or smaller or higher or larger)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:47
L9	5	(low near3 (potential or voltage)) with drain with depth with pixel	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:47
L10	73	(low near3 (potential or voltage)) with drain with depth	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:49
L11	1700	(potential or voltage or level) with drain with depth	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:50

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L12	4	4 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:50
L13	307	348/296.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:50
L14	2	13 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:51
L15	6	3 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:52
L16	1012	348/300-307.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:52
L17	25	3 and 16	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:53
L18	1	11 and 16	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:56
L19	68	reset$4 with (prim$3 adj3 effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:57
L20	3	(prim$3 adj3 effect) with afterglow	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:59
L21	7981	(prim$3 adj3 effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:59
L22	4	21 and (4 or 16)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:11

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L23	9	(electronic dj3 shutter) same (potential or voltage) same drain same reset$4 same (FD or (float$3 adj3 diffusion))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:07
L24	6	(potential or voltage) same drain same reset$4 same ((FD or (float$3 adj3 diffusion)) with depth)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:09
L25	3	(reset$4 near5 pulse) same drain same reset$4 same ((FD or (float$3 adj3 diffusion)) with depth)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:10
L26	3	(reset$4 near5 pulse) same drain same ((FD or (float$3 adj3 diffusion)) with depth)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:11
L27	3	(reset$4 near5 pulse) same ((FD or (float$3 adj3 diffusion)) with depth)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:11
L28	594	(reset$4 near5 pulse) same (FD or (float$3 adj3 diffusion))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:11
L29	72	28 and (4 or 16)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:13
L30	207	yamaguchi-takumi$5.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:17
L31	50	komobuchi-hiroyoshi$5.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 15:20
S1	309	voltage with gate with ((read or transfer) near3 transistor$1) with reset$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 14:36
S2	25	voltage with gate with ((read or transfer) near3 transistor$1) with reset$3 with (lower or smaller or higher or larger)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/17 16:28

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S3	2	(low adj4 voltage) with gate with ((read or transfer) near3 transistor$1) with reset$3 with (lower or smaller or higher or larger)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/12/10 13:54
S4	2	((low adj4 voltage) with gate with ((read or transfer) near3 transistor$1)) same (reset$3 with (lower or smaller or higher or larger))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/17 16:31
S5	36	(voltage with gate with ((read or transfer) near3 transistor$1)) same (reset$3 with (lower or smaller or higher or larger))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/17 16:31
S6	12	drain with layer$1 with (signal adj2 line$1) with (FD or storage) with (above or below or under)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:47
S7	107	drain with layer$1 with (signal adj2 line$1) with (FD or storage)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 10:52
S8	506	drain with layer$1 with optical	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:19
S9	4	drain with layer$1 with (optical near3 black)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 11:22
S10	15	drain with (optical near3 black)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:18
S11	341	257/E27.131.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:18
S12	2	S8 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:18
S13	115	S11 and (drain with layer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:32

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S14	1023	257/435.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:32
S15	106	S14 and (drain with layer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:33
S16	3	S14 and (drain with layer$1) and (optical adj3 black)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:33
S17	10	("4942474" | "4949152" | "5043783" | "5172249" | "5309013" | "5404039" | "5471515" | "5563429" | "5604364" | "5625210").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/18 08:44
S18	149	348/300.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/18 10:53
S19	19	S18 and (drain with layer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 08:47
S20	1903	drain with layer$1 with (signal adj2 line$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 11:57
S21	132	348/301.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/18 11:01
S22	2	S20 and S21	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/18 11:02
S23	424	348/302.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/18 11:01
S24	7	S20 and S23	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/18 11:02
S25	2	drain with layer$1 with (FD adj3 line)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:27
S26	315	drain with layer$1 with gate with ((detect$3 or read$3 or amplif$3) near4 transistor$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 11:11

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S27	3	S26 and (S21 or S23)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 11:09
S28	12	drain with layer$1 with gate with ((detect$3 or read$3 or amplif$3) near4 transistor$1) with (shield$3 or block$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 11:11
S29	2	(drain with layer$1) same (shield$3 with (optical near3 black))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 11:23
S30	0	(drain with layer$1) same ((block$3 or opaque) with (optical near3 black))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 12:01
S33	50	drain with layer with (power or voltage with VDD) with shield$3	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 12:05
S34	30	drain with (power or voltage with VDD) with shield$3 with light	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 12:10
S35	16	(drain with (power or voltage with VDD)) same (metal with shield$3 with light)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 12:15
S36	34	(drain with (power or voltage or VDD)) same (metal with shield$3 with light)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 12:31
S37	242	drain with metal with shield$3 with light	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 13:18
S38	168	(VDD near4 layer) same drain	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 13:13
S40	8	drain with metal with block$1 with light	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 13:23

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S41	334	drain same (block$1 near5 light)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 13:25
S42	950	CMOS same ((block$3 or shield$3) near5 light)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 13:26
S43	135	S42 and "348"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 13:33
S44	398	S42 and "257"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:14
S45	3	(FD near3 line) with ((block$3 or shield$3) near5 light)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:36
S46	52	storage with gate with transistor$1 with ((block$3 or shield$3) near5 light)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:46
S47	13	(FD near3 line) with (metal or aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:43
S51	11	storage with gate$1 with transistor$1 with (block$3 or shield$3) with metal	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:48
S52	206	storage with gate$1 with transistor$1 with lines with metal	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:49
S53	4	S52 and 348/294-332.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/08/18 14:49

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((read adj2 transistor) and storage and (detect$3 adj2 transsitor) and drain and pulse and voltage and (common adj3 gate) and (low adj3 potential) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:25
L2	0	((read adj2 transistor) and storage and (detect$3 adj2 transsitor) and drain and voltage and (common adj3 gate) and (low adj3 potential) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:25
L3	0	((read adj2 transistor) and storage and (detect$3 adj2 transsitor) and drain and voltage and (low adj3 potential) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:26
L4	0	((read adj2 transistor) and (detect$3 adj2 transsitor) and drain and voltage and (low adj3 potential) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:26
L5	1	(drain and voltage and (low adj3 potential) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:26
L6	1	(drain and (low adj3 potential) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:26
L7	2	(drain and (low adj3 level) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:27
L8	2	(drain and (low adj3 voltage) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:27
L9	20	(drain and (potential or voltage or level) and reset$4 and depth).CLM.	US-PGPUB	OR	ON	2006/12/10 15:27

Interference Search History Printout, LN